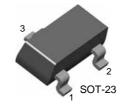


## **MMBT3904K**

## **NPN Epitaxial Silicon Transistor**

## **General Purpose Transistor**





1. Base 2. Emitter 3. Collector

## Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	200	mA
P <sub>C</sub>	Collector Power Dissipation	350	mW
T <sub>J,</sub> T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 ~ 150	°C

## **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	60		V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_C = 1 \text{mA}, I_B = 0$	40		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	6		V
I <sub>CEX</sub>	Collector Cut-off Current	V <sub>CE</sub> = 30V, V <sub>EB</sub> = 3V		50	nA
h <sub>FE</sub>	DC Current Gain *	$V_{CE} = 1V$ , $I_{C} = 0.1 \text{mA}$ $V_{CE} = 1V$ , $I_{C} = 1 \text{mA}$ $V_{CE} = 1V$ , $I_{C} = 10 \text{mA}$ $V_{CE} = 1V$ , $I_{C} = 50 \text{mA}$ $V_{CE} = 1V$ , $I_{C} = 100 \text{mA}$	40 70 100 60 30	300	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage *	$I_C = 10$ mA, $I_B = 1$ mA $I_C = 50$ mA, $I_B = 5$ mA		0.2 0.3	V V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage *	$I_C = 10$ mA, $I_B = 1$ mA $I_C = 50$ mA, $I_B = 5$ mA	0.65	0.85 0.95	V V
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 5V, I_{E} = 0, f = 1MHz$		4	pF
f <sub>T</sub>	Current Gain-Bandwidth Product	V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA, f = 100MHz	300		MHz
NF	Noise Figure	$I_C$ = 100μA, $V_{CE}$ = 5V, $R_S$ = 1KΩ $f$ = 10Hz to 15.7KHz		5	dB
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> = 3V, V <sub>BE</sub> = 0.5V I <sub>C</sub> = 10mA, I <sub>B1</sub> = 1mA		70	ns
t <sub>OFF</sub>	Turn Off Time	$V_{CC} = 3V, I_{C} = 10mA, I_{B1} = I_{B2} = 1mA$		250	ns

<sup>\*</sup> Pulse Test: Pulse Width $\leq$ 300 $\mu$ s, Duty Cycle $\leq$ 2%

### **Typical Performance Characteristics**

Figure 1. DC current Gain

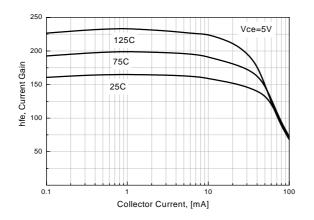


Figure 2. Collector-Emitter Saturation Voltage

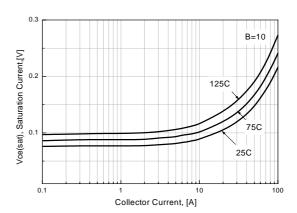


Figure 3. Base-Emitter Saturation Voltage

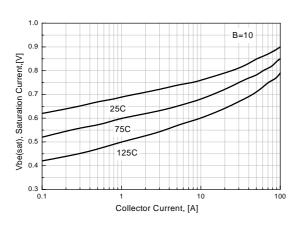


Figure 4. Collector - Base Leakage Current

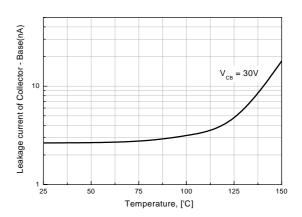


Figure 5. Output Capacitance

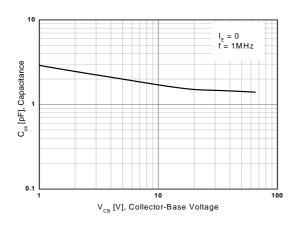
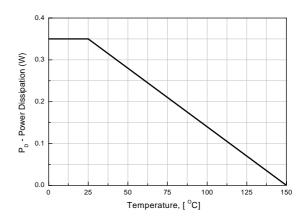


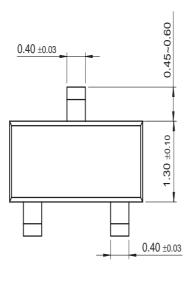
Figure 6. Power Dissipation vs
Ambient Temperature

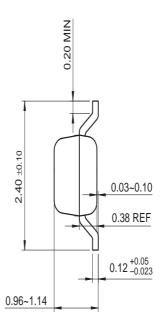


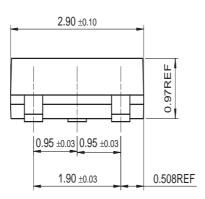
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## **Mechanical Dimensions**

# SOT-23







Dimensions in Millimeters

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